

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application. Please cancel claims 81-84, 93-98, and 102-107, as follows:

Listing of Claims:

1-79. (Cancelled)

80. (Previously Presented) A method of treating a wafer, comprising:  
depositing a first conductive layer over the wafer;  
depositing a second conductive layer over the wafer;  
exposing the second conductive layer in situ to a reducing environment; and  
exposing the second conductive layer to a material comprising HCl, wherein the first conductive layer comprises hemispherical silicon grain and wherein the second conductive layer comprises tungsten nitride.

81.-84 (Cancelled)

85-87. (Cancelled)

88. (Previously Presented) A method of treating a wafer, comprising:  
depositing a first conductive layer over the wafer;  
depositing a second conductive layer over the wafer;  
exposing the second conductive layer to a reducing environment;  
and  
passivating the second conductive layer by exposing the second conductive layer to a material comprising HCl, wherein the first conductive layer comprises hemispherical silicon grain and wherein the second conductive layer comprises tungsten nitride.

89. (Cancelled)

90. (Previously Presented) The method of claim 88 further comprising forming a third conductive layer on the second conductive layer.

91. (Previously Presented) The method of claim 90 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

92. (Previously Presented) The method of claim 91 wherein the third conductive layer comprises polysilicon.

93.-98. (Cancelled)

99. (Previously Presented) The method of claim 80 wherein exposing the second conductive layer in situ to a reducing environment comprises exposing the second conductive layer to silane gas.

100. (Previously Presented) The method of claim 80 wherein exposing the second conductive layer to a material comprising HCl comprises exposing the second conductive layer to this selection prior to exposing the second conductive layer in situ to a reducing environment.

101. (Previously Presented) The method of claim 80 wherein exposing the second conductive layer to a material comprising HCl comprises exposing the second conductive layer to this selection prior to depositing the first conductive layer.

102.-107 (Cancelled)

108. (Previously Presented) The method of claim 88 wherein exposing the second conductive layer to a reducing environment comprises exposing the second conductive layer to silane gas.

109. (Previously Presented) The method of claim 88 wherein exposing the second conductive layer to a material comprising HCl comprises exposing the second conductive layer to this selection prior to exposing the second conductive layer to a reducing environment.

110. (Previously Presented) The method of claim 88 wherein exposing the second conductive layer to a material comprising HCl comprises exposing the second conductive layer to this selection prior to depositing the first conductive layer.